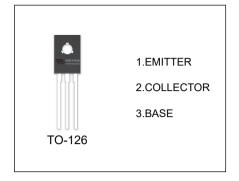


2SD2136 TRANSISTOR (NPN)

FEATURES

- High Forward Current Transfer Ratio h_{FE} Which has
- Allowing Supply with the Radial Taping



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SD2136	TO-126	Bulk	200pcs/Bag
2SD2136-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current	3	А
Pc	Collector Power Dissipation	1.25	W
R _{0JA}	Thermal Resistance From Junction To Ambient	100	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA,I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =30mA,I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA,I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =60V,I _E =0			200	μA
Collector cut-off current	I _{CEO}	V _{CE} =60V,I _B =0			300	μA
Emitter cut-off current	I _{EBO}	V _{EB} =6V,I _C =0			1	mA
DC comment acin	h _{FE(1)} *	V _{CE} =4V, I _C =1A	40		250	
DC current gain	h _{FE(2)} *	V _{CE} =4V, I _C =3A	10			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =3A,I _B =0.375A			1.2	V
Base-emitter voltage	V _{BE} *	V _{CE} =4V, I _C =3A			1.8	V
Transition frequency	f _T	V _{CE} =5V,I _C =0.1A, f=10MHz		30		MHz

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

CLASSIFICATION OF h_{FE(1)}

RANK	Р	Q	R
RANGE	40-90	70-150	120-250



